# NSN 5961-01-332-1145

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# Inclosure Material:

Metal and glass

# **Overall Length:**

1.550 inches

# **Overall Height:**

Between 0.250 inches and 0.300 inches

# Overall Width:

1.050 inches

# **Mounting Facility Quantity:**

2

#### Internal Configuration:

Junction contact

# Joint Electronic Device Engineering Council/jedec/case Outline Designation:

#### To-3

## Electrode Internally-electrically Connected To Case:

Collector

#### Mounting Method:

Unthreaded hole

## Semiconductor Material:

Silicon

## Voltage Rating In Volts Per Characteristic:

800.0 breakdown voltage, collector to emitter, sustained and 1400.0 collector-to-emitter, with voltage between base and emitter and 8.0 emitter to base voltage, dc

## **Current Rating Per Characteristic:**

2.50 amperes source cutoff current and 2.00 amperes source cutoff current

## Power Rating Per Characteristic:

125.0 watts small-signal input power, common-collector preset

## Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

#### **Special Features:**

Junction pattern arrangement: npn

#### Terminal Type And Quantity:

2 pin and 1 case

#### Shelf Life:

N/a

#### Unit Of Measure:

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## Demilitarization:

No

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